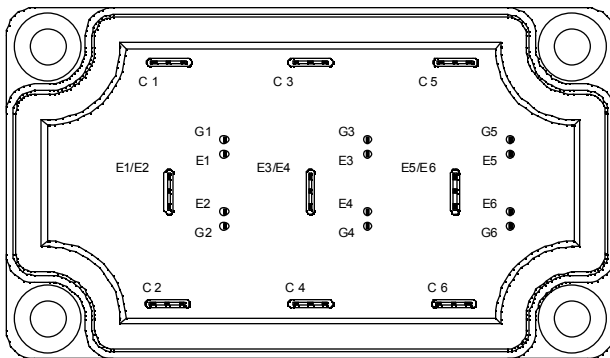
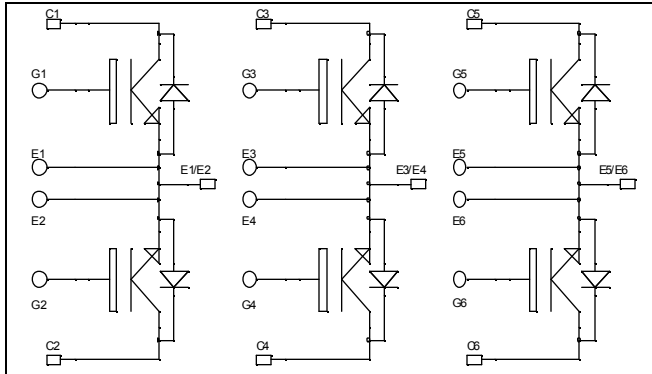


Triple dual Common Source NPT IGBT Power Module

$V_{CES} = 600V$
 $I_C = 90A @ T_c = 80^\circ C$



Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features


- Non Punch Through (NPT) Fast IGBT[®]
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Easy paralleling due to positive TC of VCESat
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	110
		$T_c = 80^\circ C$	90
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	315
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	416
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	200A @ 600V

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$ $V_{CE} = 600\text{V}$			250 500	μA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 90\text{A}$		2.0 2.2	2.5	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1\text{mA}$	3		5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			± 150	nA

Dynamic Characteristics

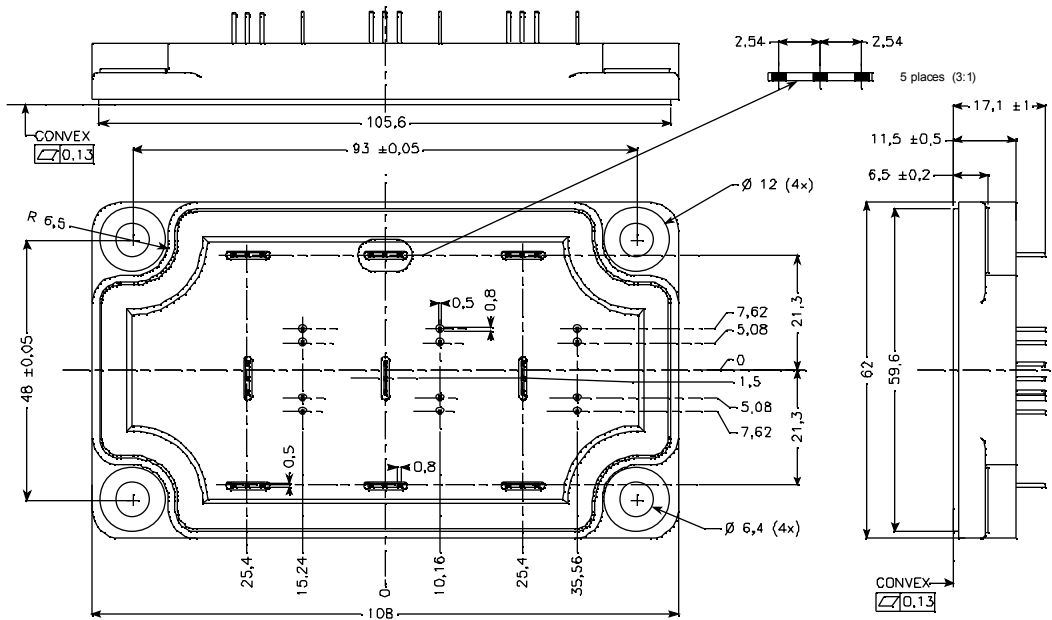
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		4300		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		470		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		400		
Q_g	Total gate Charge	$V_{GE} = 15\text{V}$		330		nC
Q_{ge}	Gate – Emitter Charge	$V_{Bus} = 300\text{V}$		290		
Q_{gc}	Gate – Collector Charge	$I_C = 90\text{A}$		200		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		26		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$		25		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400\text{V}$		150		
T_f	Fall Time	$I_C = 90\text{A}$ $R_G = 5\ \Omega$		30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		26		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$		25		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400\text{V}$		170		
T_f	Fall Time	$I_C = 90\text{A}$ $R_G = 5\ \Omega$		40		
E_{on}	Turn-on Switching Energy	$V_{GE} = 15\text{V}$ $V_{Bus} = 400\text{V}$		4.3		mJ
E_{off}	Turn-off Switching Energy	$I_C = 90\text{A}$ $R_G = 5\ \Omega$		3.5		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$			250 500	μA
I_F	DC Forward Current			60		A
V_F	Diode Forward Voltage	$I_F = 60\text{A}$		1.6	1.8	V
		$I_F = 120\text{A}$		1.9		
		$I_F = 60\text{A}$ $T_j = 125^\circ\text{C}$		1.4		
t_{rr}	Reverse Recovery Time	$I_F = 60\text{A}$ $V_R = 400\text{V}$		130 170		ns
		$di/dt = 200\text{A}/\mu\text{s}$				
Q_{rr}	Reverse Recovery Charge			220 920		nC
		$T_j = 125^\circ\text{C}$				

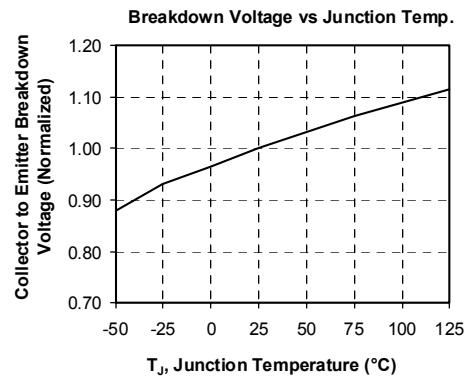
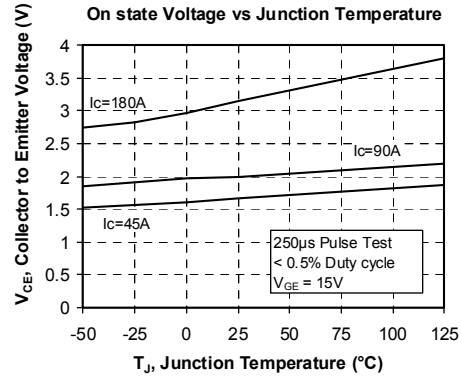
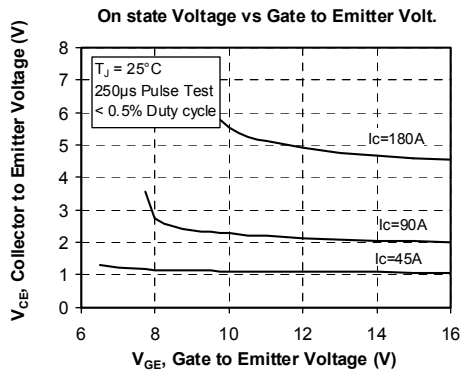
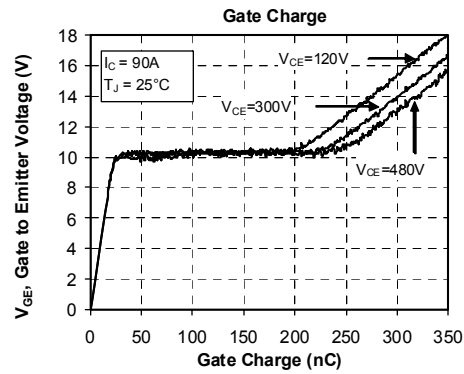
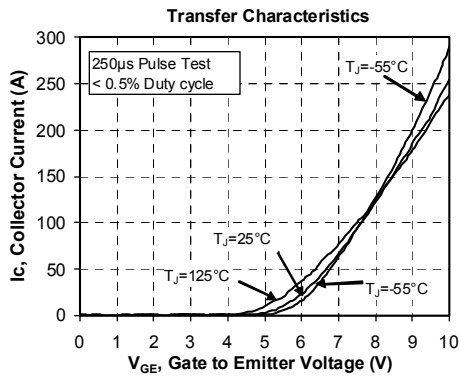
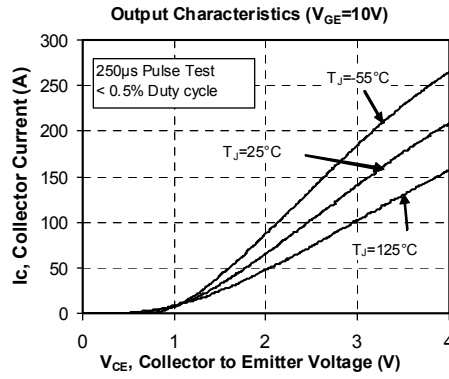
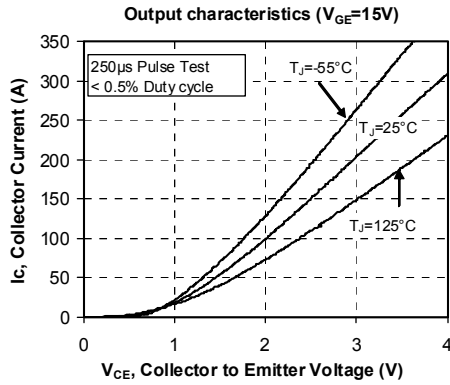
Thermal and package characteristics
Symbol Characteristic

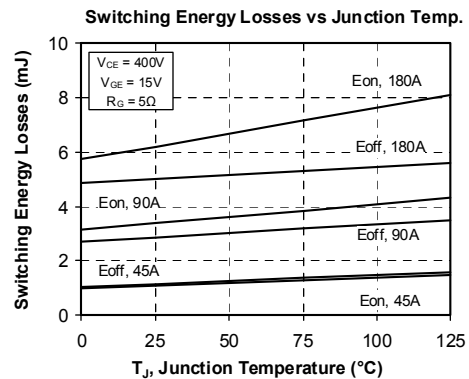
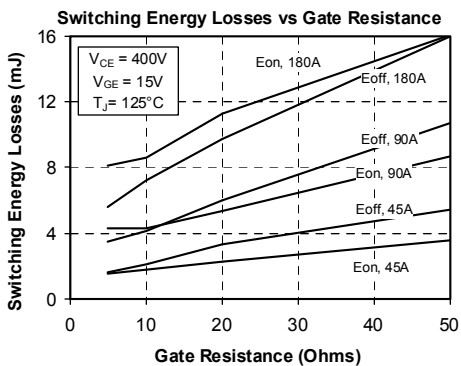
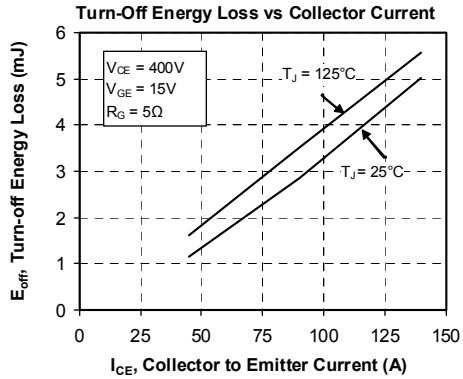
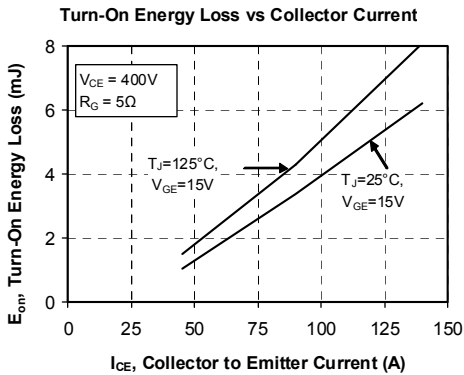
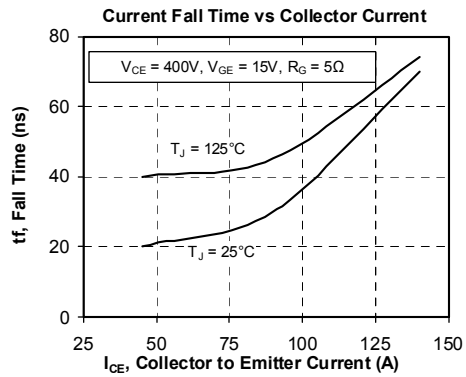
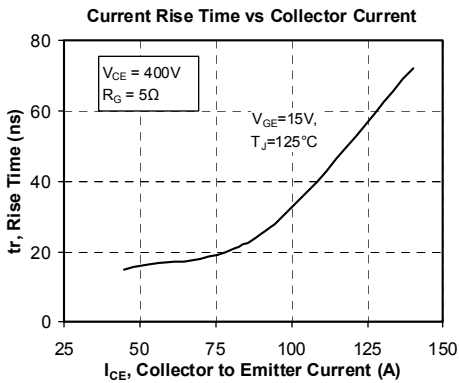
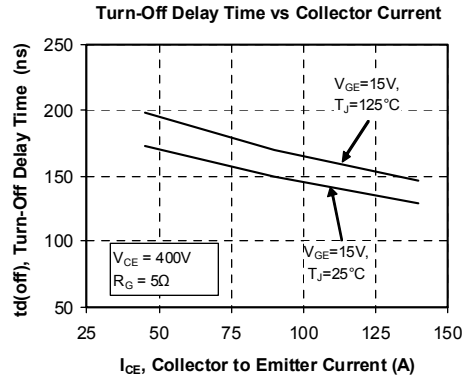
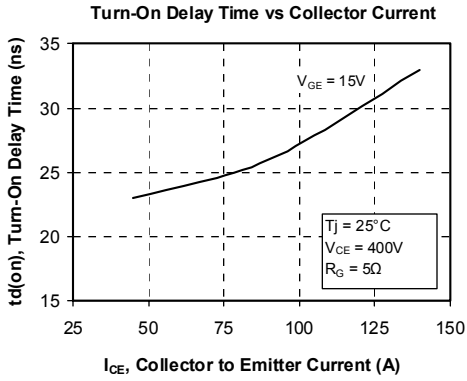
		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>	
R _{thJC}	Junction to Case Thermal Resistance	IGBT		0.3	°C/W	
		Diode		0.9		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Wt	Package Weight				250	g

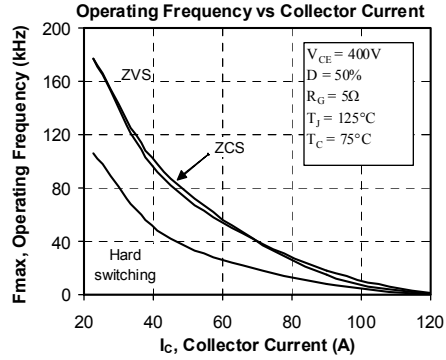
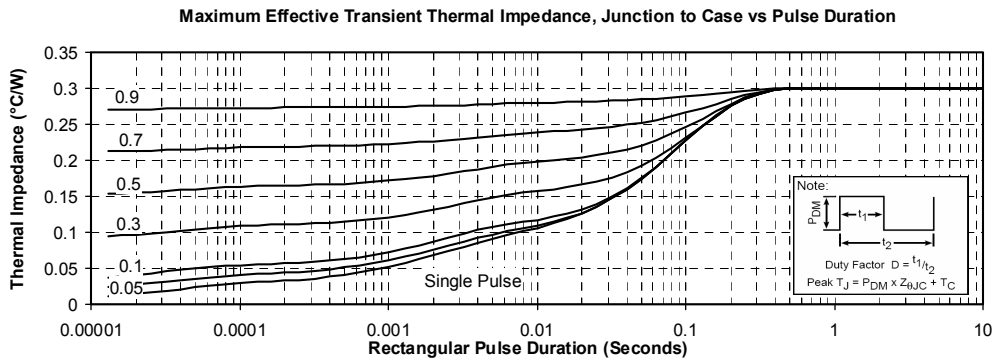
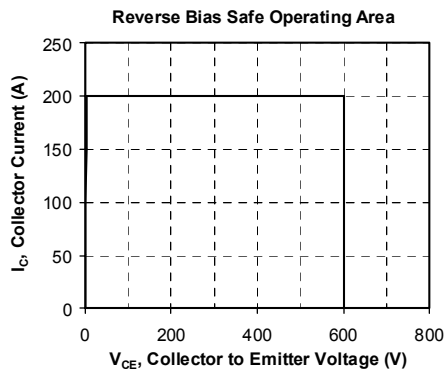
SP6-P Package outline (dimensions in mm)


See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

Typical Performance Curve







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